



Product data sheet

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SOD-123FL

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

P/N	ES1AW	ES1BW	ES1CW	ES1DW	ES1EW	ES1GW	ES1JW	UNITS
MARK		E1B	E1C	E1D	E1E	E1G	E1J	V
Maximum Recurrent Peak Reverse Voltage		100	150	200	300	400	600	V
Maximum RMS Voltage		70	105	140	210	280	420	V
Maximum DC Blocking Voltage		100	150	200	300	400	600	
Maximum Average Forward Rectified Current at Ta=25°C	1.0			А				
Peak Forward Surge Current, 8.3 ms single half sine-wave								
superimposed on rated load (JEDEC method)		30					А	
Maximum Instantaneous Forward Voltage at 1.0A			0.95		1.2	5	1.7	V
Maximum DC Reverse Current Ta=25°C				5.0				μA
at Rated DC Blocking Voltage Ta=100°C				500				μA
Maximum Reverse Recovery Time (Note 1)		35					nS	
Typical Junction Capacitance (Note 2) 15				pF				
Typical Thermal Resistance R JA (Note 3)		80					°C/W	
Operating and Storage Temperature Range TJ, Tstg		-65+150					°C	

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal Resistance from Junction to Ambient.



ES1AW THRU ES1JW 🖽 🐼

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FIG.1- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE 🔶 trr 🄶 50 NONINDUCTIVE 10 NONINDUCTIVE +0.5A AVERAGE FORWARD CURRENT, (A) 1.2 -111 w 1.0 (+) 0 D.U.T. 25Vdc (approx.) 0.8 늧 GENERATOF (NOTE 2) -0.25A (--) 0.6 Single Phase (+) Half Wave 60Hz OSCILLISCOPE ര NON-INDUCTIVE ≷ stive Or Inductive L (NOTE 1) 0.4 0.375"(9.5mm) Lead Length 0.2 -1.0A NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF ▶ _{1cm} ► 0⊾ 0 2. Rise Time= 10ns max., Source Impedance= 50 ohms SET TIME BASE FOR 25 50 75 100 125 150 175 AMBIENT TEMPERATURE,(°C) 50 / 10ns / cm FIG.3-TYPICAL FORWARD FIG.4-TYPICAL REVERSE CHARACTERISTICS CHARACTERISTICS 50 50 INSTANTANEOUS FORWARD CURRENT,(A) 10 REVERSE LEAKAGE CURRENT, (µA) 10 3.0 3.0 1.0 1.0 Tj=100°C Tj=25°C Ti=25°C 0.1 ulse Width 300us 1% Duty Cycle 0.1 .01 .01 .4 .6 1.0 1.2 1.4 1.6 1.8 0 20 40 60 80 100 120 140 .8 PERCENT OF RATED PEAK REVERSE VOLTAGE,(%) FORWARD VOLTAGE,(V) FIG.5-MAXIMUM NON-REPETITIVE FORWARD FIG.6-TYPICAL JUNCTION CAPACITANCE SURGE CURRENT 175 50 PEAK FORWARD SURGE CURRENT,(A) 150 JUNCTION CAPACITANCE, (pF) 40 125 100 30 8.3ms Single Half Tj=25°C 75 20 Sine Wave JEDEC method 50 10 25 0 0 .01 .05 .5 5 10 50 100 .1 1 1 5 10 50 100 NUMBER OF CYCLES AT 60Hz REVERSE VOLTAGE,(V)

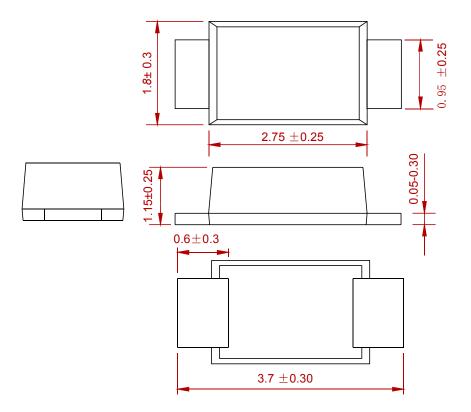
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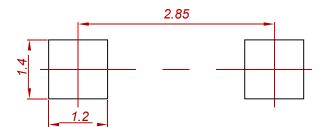
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PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
ES1AW THRU ES1JW	SOD-123FL	3000



ES1AW THRU ES1JW

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